MINI-MELF-SMD

Applications

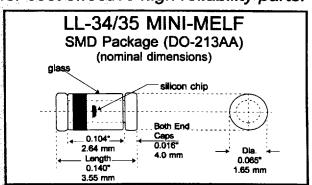
LL4150 or 1N4150UR-1

Silicon Diode Switching

Used in general purpose applications, where a low current controlled forward characteristic and fast switching speed are important. BKC can produce generic equivalents to JAN/ TX/ TXV and S level per MIL-S-19500/ 437 with internal source control drawings. Use HR, HRX, HRV or HRS suffixes for cost effective high reliability parts.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability
- Available in DO-35 package with approval to Mil-S-19500 / 437



Maximum Ratings			Symbol	Value	Unit
Peak Inverse Voltage @ 5μA & 0.1μA @ -55 °C			PIV	75 (Min.)	Volts
Average Rectified Current			l _{Avg}	200	mAmps
Continuous Forward Current			I _{Fdc}	400	mAmps
Peak Surge Current (t _{peak} = 1 Sec.)			peak	0.50	Amp
Power Dissipation T _{End Cap} = 50 °C			P _{tot}	500	mWatts
Operating and Storage Temperature Range			T _{Op & St}	-65 to +175	°C
Electrical Characteristics @ 25 °C	Symbol	Minimum		Maximum	Unit
Forward Voltage Drop @ I _F = 100 μA	V _F	0.49		0.55	Volts
Forward Voltage Drop @ I _F = 1.0 mA	V _F	0.54		0.62	Volts
Forward Voltage Drop @ I _F = 10 mA	V _F	0.66		0.74	Volts
Forward Voltage Drop @ I _F = 50 mA	V _F	0.76		0.86	Volts
Forward Voltage Drop @ I _F = 100 mA	V _F	0.82		0.92	Volts
Forward Voltage Drop @ I _F = 200 mA	V _F	0.87		1.00	Volts
Reverse Leakage Current @ V _R = 50 V	I _B			100	nA
Reverse Leakage Current @ V _R = 50 V				100 @ 150 °C	μA
Capacitance @ V _R = 0 V, f = 1mHz	C _T			2.5	pF
Reverse Recovery Time (note 1)	t _{rr}			4.0	nSecs

Note 1: Per Method 4031-B with $I_F = I_R = 10$ mA, $R_L = 100$ Ohms, C = 3 Pf..

For equivalent MIL devices, use 1N4150UR-1 along with the appropriate HR, HRX, HRV or HRS suffix.

The SMD DO-213AA also comes in a commercial and a military DO-35 leaded version (1N4150).

 \widehat{BKC}

BKC Semiconductors Inc.

6 Lake St · Lawrence, MA · 01841 · tel: (978) 681-0392 · fax: (978) 681-9135

1179983 0000629 024

56